

# Probing Materials Response to Extreme Environments

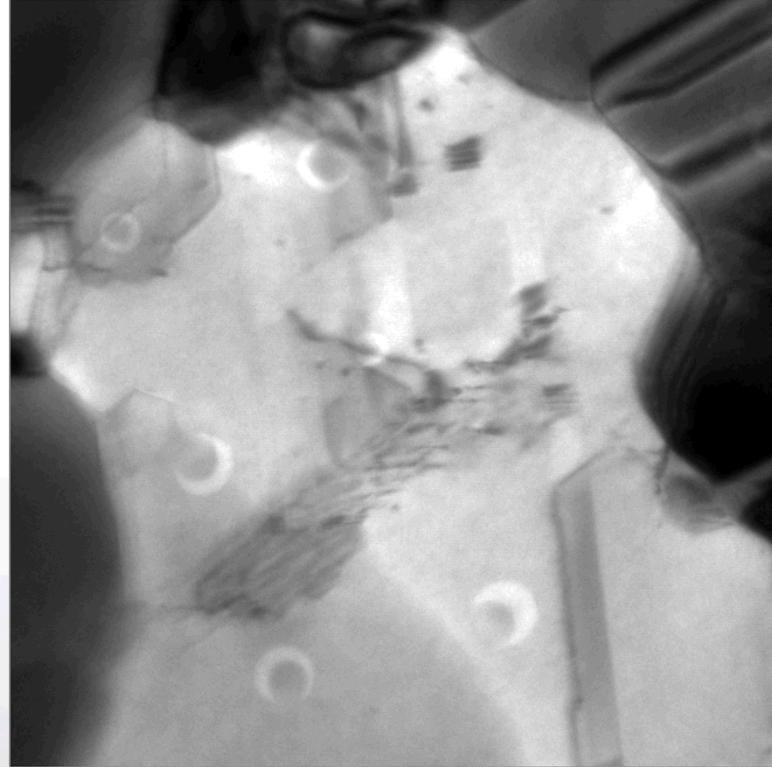
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Ion Beam Lab at Sandia National Laboratories

Nov. 10, 2015

*In situ* TEM microscopy  
Has recently undergone significant growth providing capabilities to investigate the structural evolution that occurs due to various extreme environments and combinations thereof



## Collaborators:

- IBL: D.C. Bufford, D. Buller, C. Chisholm, B.G. Clark, B.L. Doyle, S. H. Pratt, & M.T. Marshall
- Sandia: B. Boyce, T.J. Boyle, P.J. Cappillino, J.A. Scott, B.W. Jacobs, M.A. Hekmaty, D.B. Robinson, E. Carnes, J. Brinker, D. Sasaki, J.A. Sharon, T. Nenoff, W.M. Mook
- External: A. Minor, L.R. Parent, I. Arslan, H. Bei, E.P. George, P. Hosemann, D. Gross, J. Kacher, & I.M. Robertson

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# Sandia's Extreme Environment History

- 50+ years history probing radiation-solid interactions
  - Fundamental ion-solid understanding
  - Electronic system response to intense pulsed n/γ environments
  - Tritium containing materials
  - Fission/fusion reactor materials

VOLUME 16, NUMBER 3

APPLIED PHYSICS LETTERS

1 FEBRUARY 1970

## RADIATION EFFECTS IN SEMICONDUCTORS

Proceedings of the Santa Fe Conference on Radiation Effects in Semiconductors, held October 3-5, 1967

Edited by F. L. Vook

Sandia Laboratories, Albuquerque, New Mexico

The field of radiation effects in semiconductors has rapidly advanced in recent years and substantial amounts of applicable evidence have been amassed.

IEEE TRANSACTIONS ON NUCLEAR SCIENCE, VOL. 53, NO. 6, DECEMBER 2006

## Damage Equivalence of Heavy Ions in Silicon Bipolar Junction Transistors

E. Bielejec, G. Vizkelethy, N. R. Kolb, D. B. King, and B. L. Doyle

### ION IMPLANTATION DEPTH DISTRIBUTIONS: ENERGY DEPOSITION INTO ATOMIC PROCESSES AND ION LOCATIONS\*

David K. Brice

*Sandia Laboratories, Albuquerque, New Mexico 87115*

(Received 20 October 1969; in final form 11 December 1969)

### SATURATION AND ISOTOPIC REPLACEMENT OF DEUTERIUM IN LOW-Z MATERIALS\*

B.L. DOYLE, W.R. WAMPLER, D.K. BRICE and S.T. PICRAUX

*Sandia National Laboratories†, Albuquerque, New Mexico 87185, USA*

J. Nucl. Materials 93&94, 551 (1980)

Other SNL talks by Brandom Aguirre (this session) and Jose Pacheco (Friday session)



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# New Capabilities for *In Situ* Extreme Environments

## ■ TEM with dual, co-linear ion beams

- Dual tilt, Heating, Tomography
- Gas and Liquid Cells
- Hysitron mechanical test stage
- Precession Diffraction

## ■ Meso-Scale Mechanical Test with Ion Irradiation

- High Temperature (800C)
- ASTM-standard sample geometry
- 4.5MeV protons penetrate through 50um Cu samples

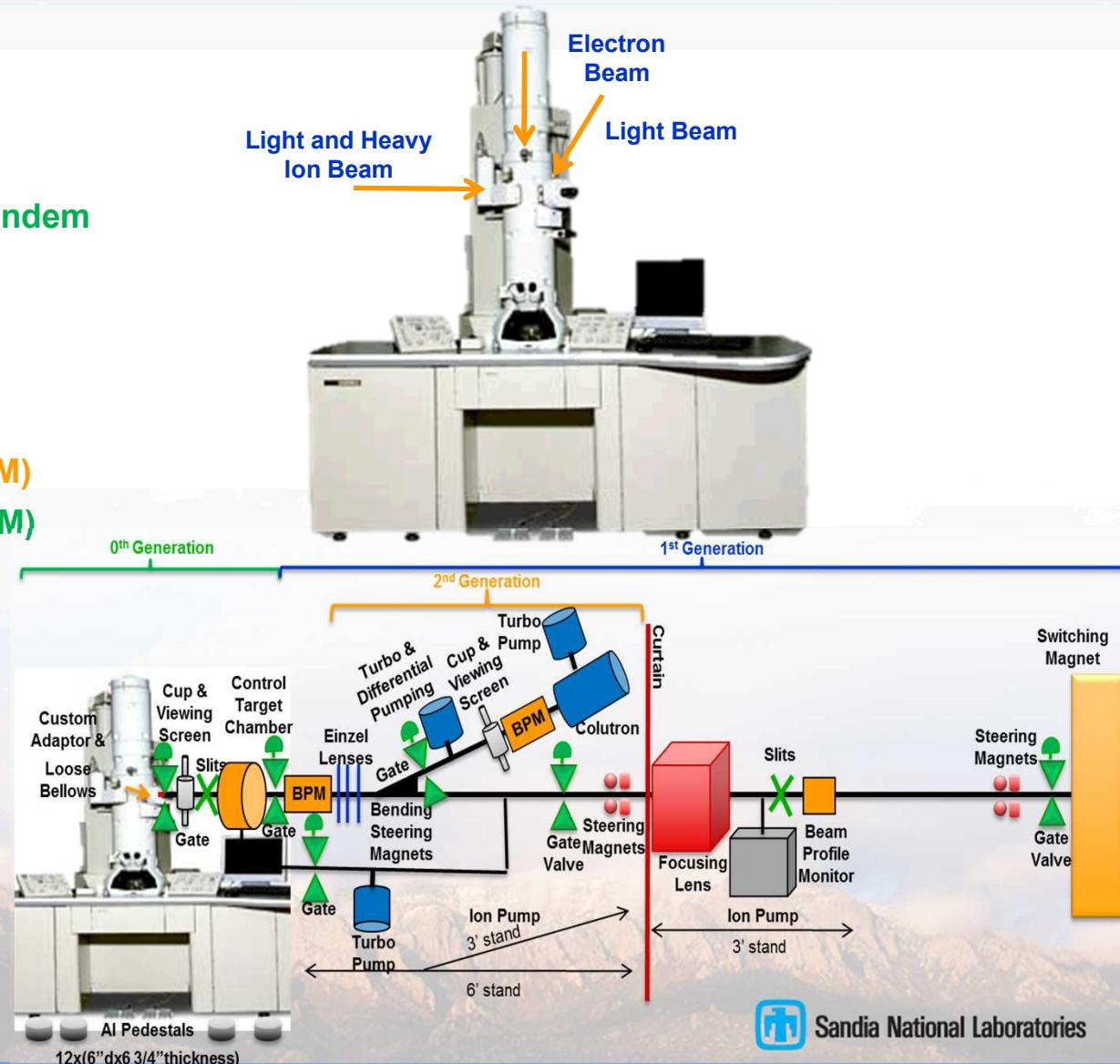


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# In situ Ion Irradiation TEM Facility

## Capabilities:

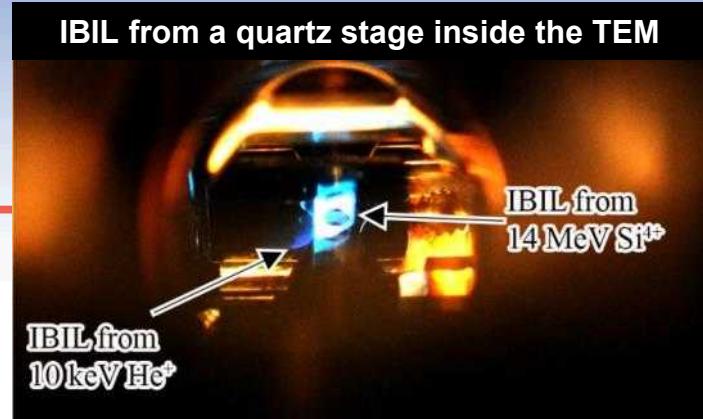
- 200 kV LaB<sub>6</sub> TEM
- Ion beams used:
  - Range of Sputtered Ions from Tandem
  - 10 keV D<sub>2</sub><sup>+</sup>
  - 10 keV He<sup>+</sup>
  - (Simultaneous D<sub>2</sub>+He)
- All beams hit same location
- Nanosecond time resolution (DTEM)
- Procession scanning (EBSD in TEM)
- In situ CL, and IBIL, and PL
- In situ vapor phase stage
- In situ liquid mixing stage
- In situ heating
- Tomography stage (2 axis)
- In situ straining stage
- In situ cooling stage
- In situ electrical bias stage



# Sandia's Concurrent *In situ* Ion Irradiation TEM Facility

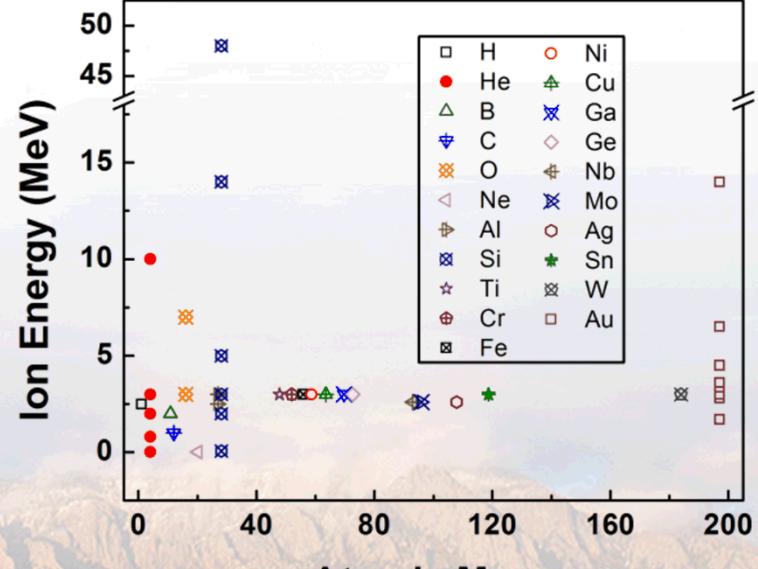
Collaborator: D.L. Buller

6 MV Tandem - 10 kV Colutron - 200 kV TEM



Direct real time observation  
of ion irradiation,  
ion implantation, or both  
with nanometer resolution

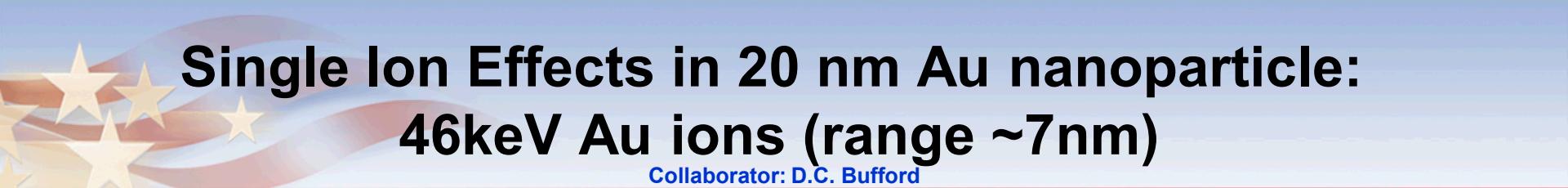
Ion species & energy introduced into the TEM



Atomic Mass

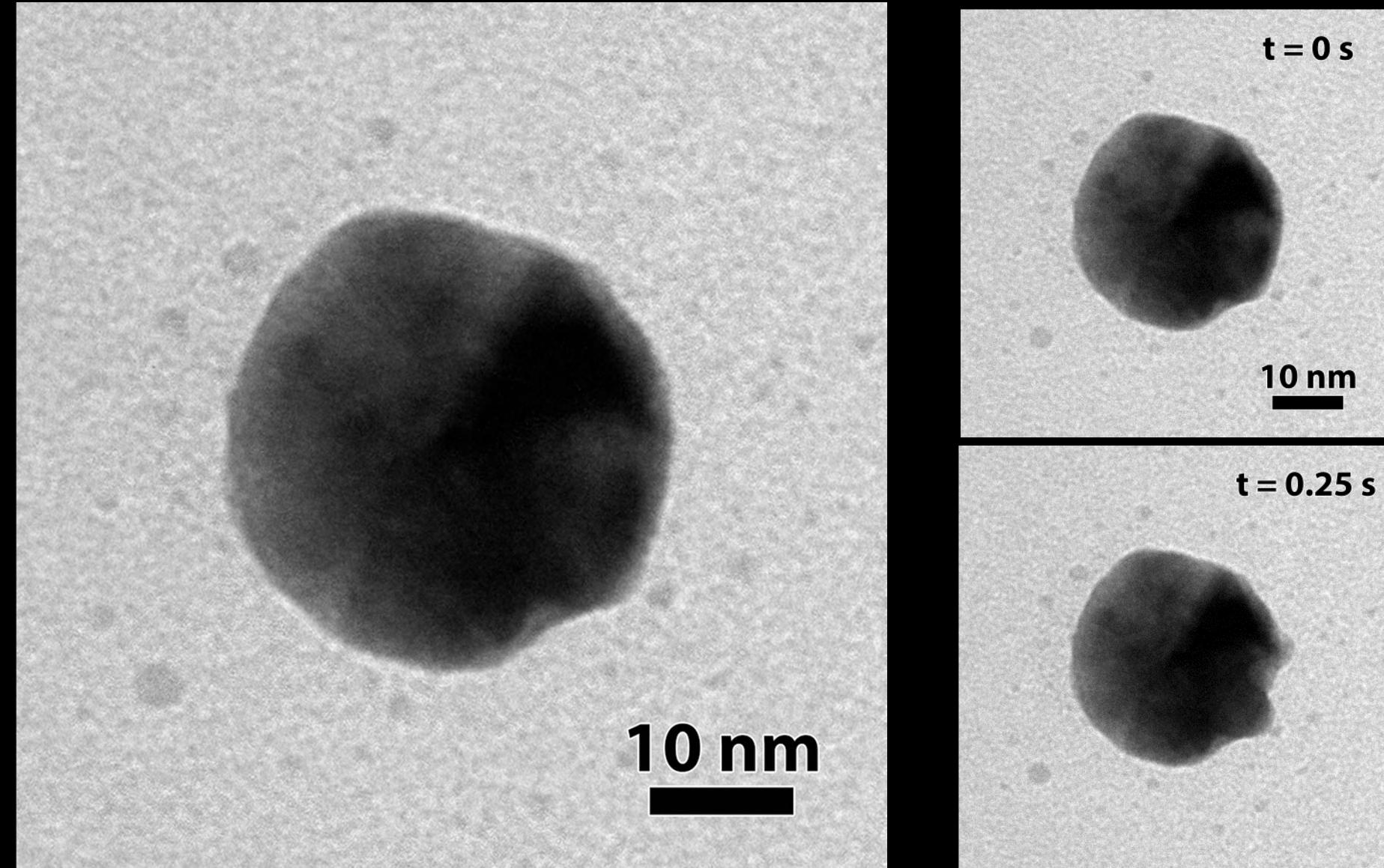


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# Single Ion Effects in 20 nm Au nanoparticle: 46keV Au ions (range ~7nm)

Collaborator: D.C. Bufford

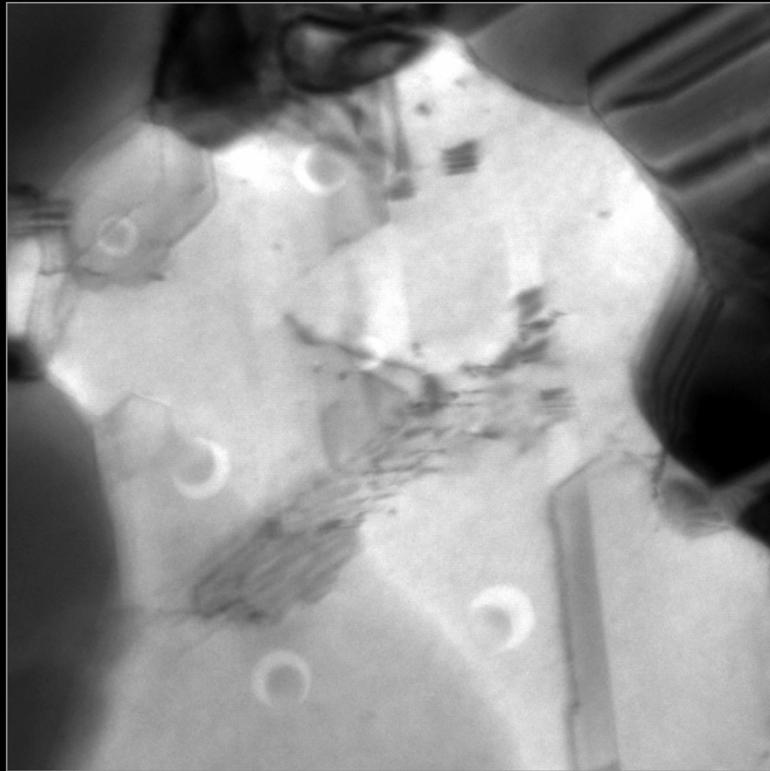




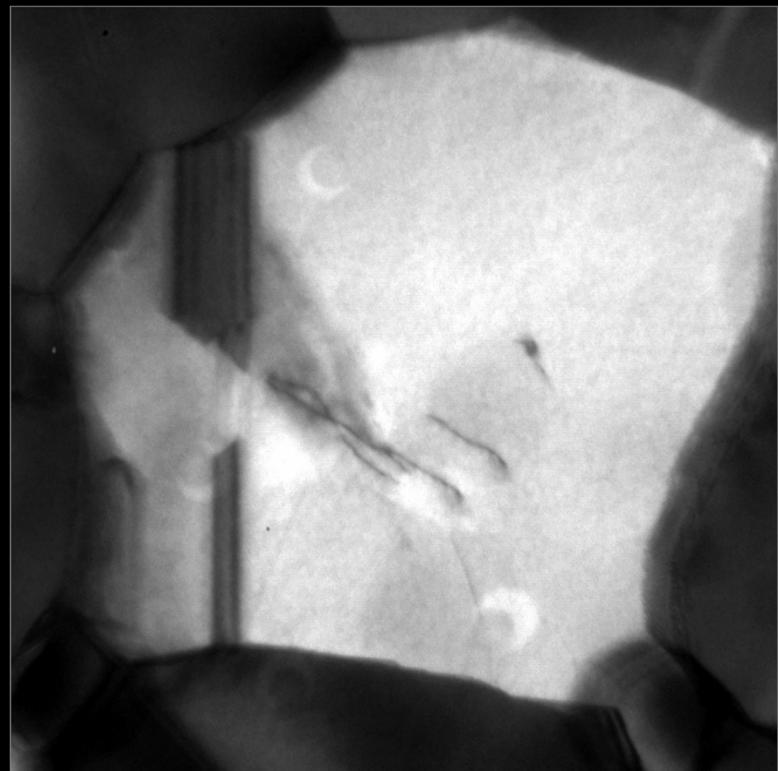
# Single Ion Strikes – 2.8MeV Au<sup>4+</sup> into/through Au film

Collaborators: C. Chisholm & A. Minor

$7.9 \times 10^9$  ions/cm<sup>2</sup>/s



$6.7 \times 10^7$  ions/cm<sup>2</sup>/s

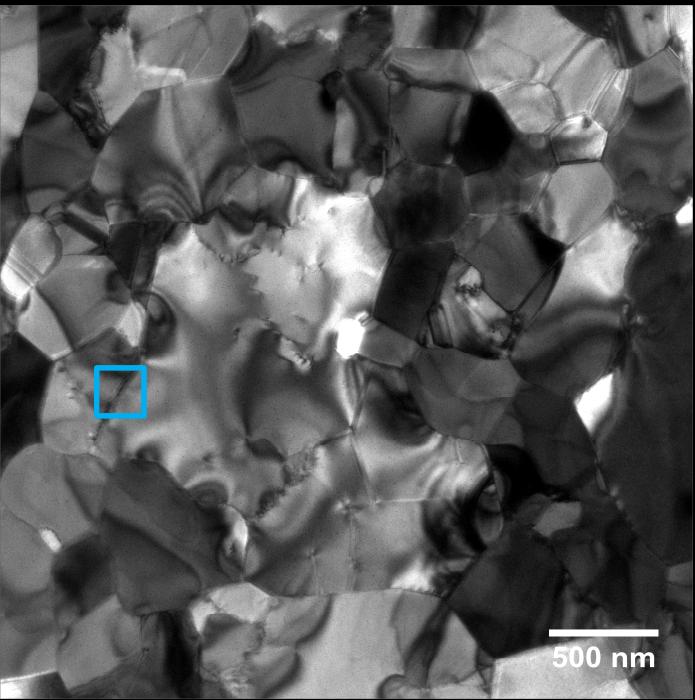


VS

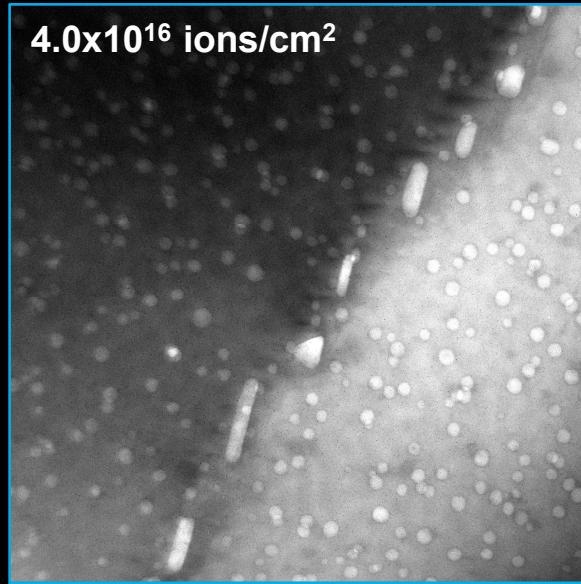
Improved vibrational and ion beam stability permits us to work at 120kx or higher permitting imaging of single cascade events

# *In situ* Implantation

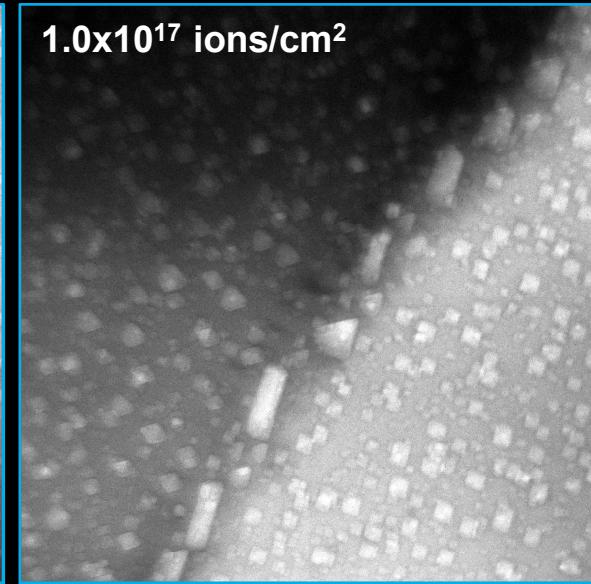
Collaborators: C. Chisholm & A. Minor



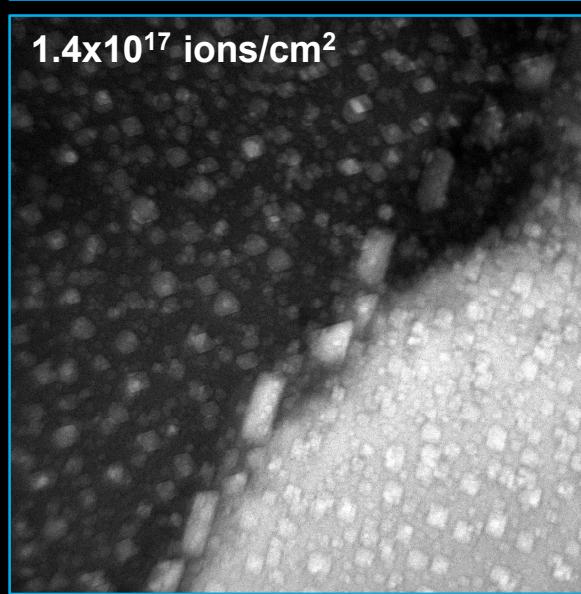
$4.0 \times 10^{16}$  ions/cm<sup>2</sup>



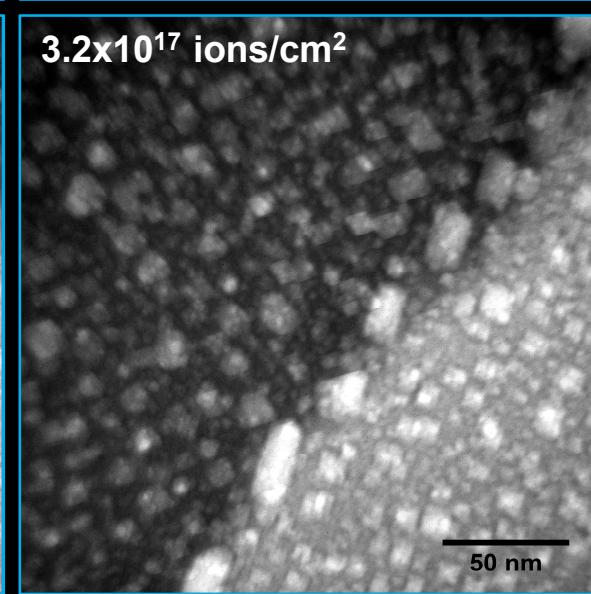
$1.0 \times 10^{17}$  ions/cm<sup>2</sup>



$1.4 \times 10^{17}$  ions/cm<sup>2</sup>



$3.2 \times 10^{17}$  ions/cm<sup>2</sup>



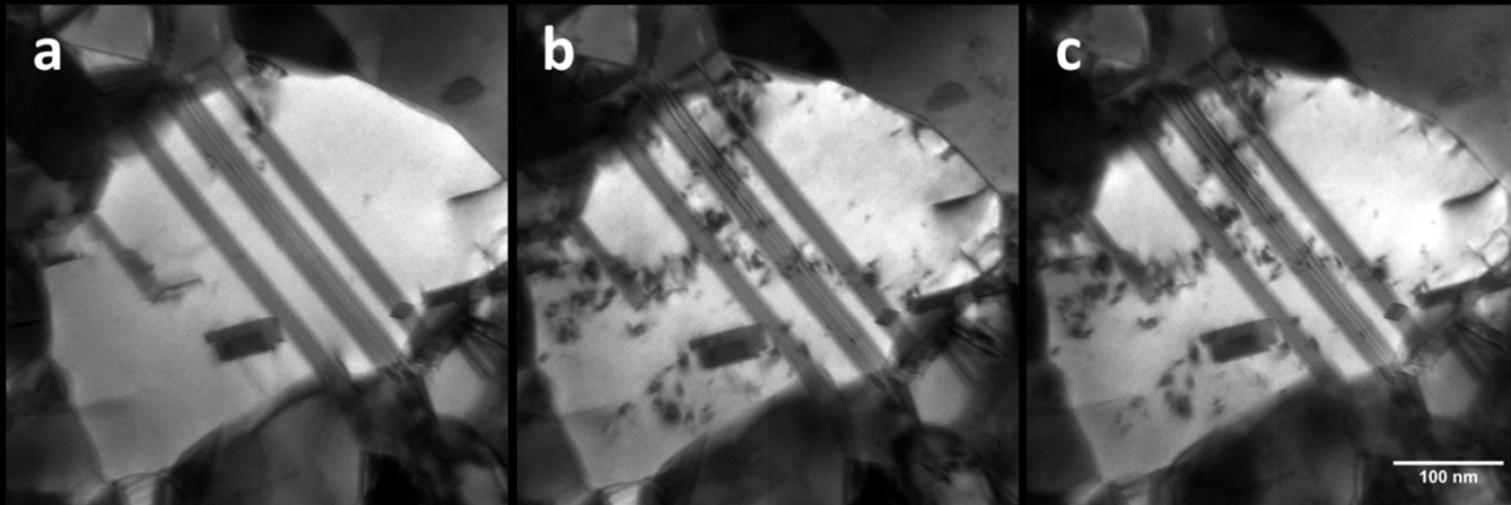
Au implanted with 10keV He<sup>+</sup>

He bubble formation on grain boundary and in the bulk

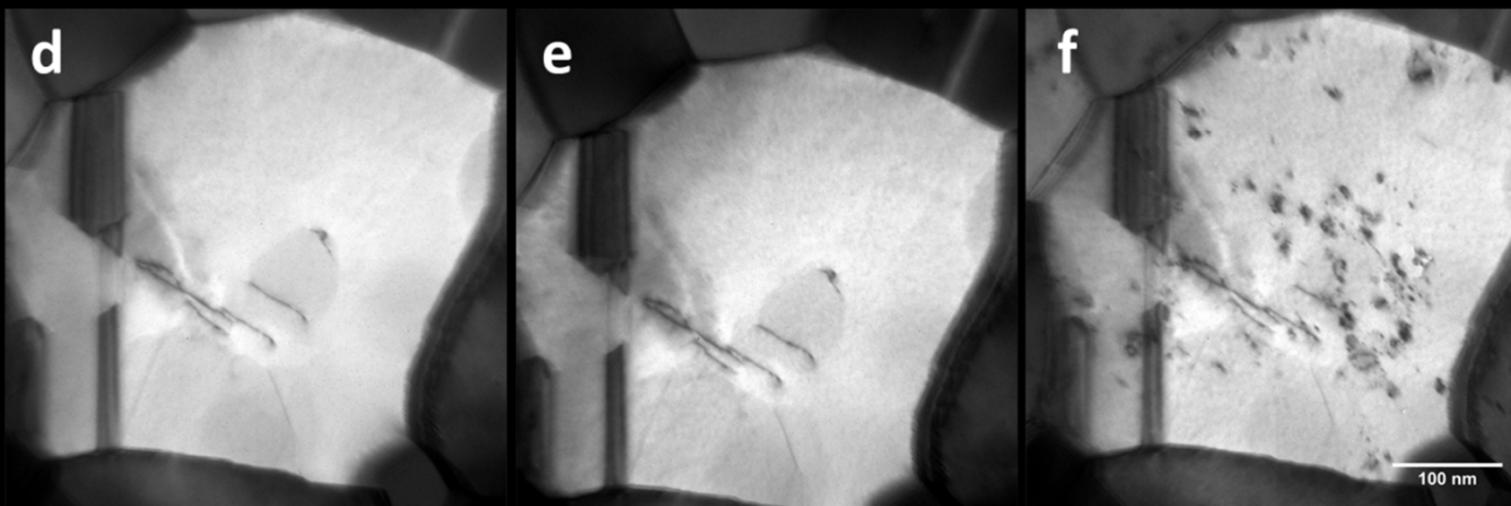
# *In situ* Successive Implantation then Irradiation (2.8MeV Au<sup>4+</sup>, 10keV He<sup>+</sup>)

Collaborators: C. Chisholm & A. Minor

Successive Au<sup>4+</sup> then He<sup>1+</sup>



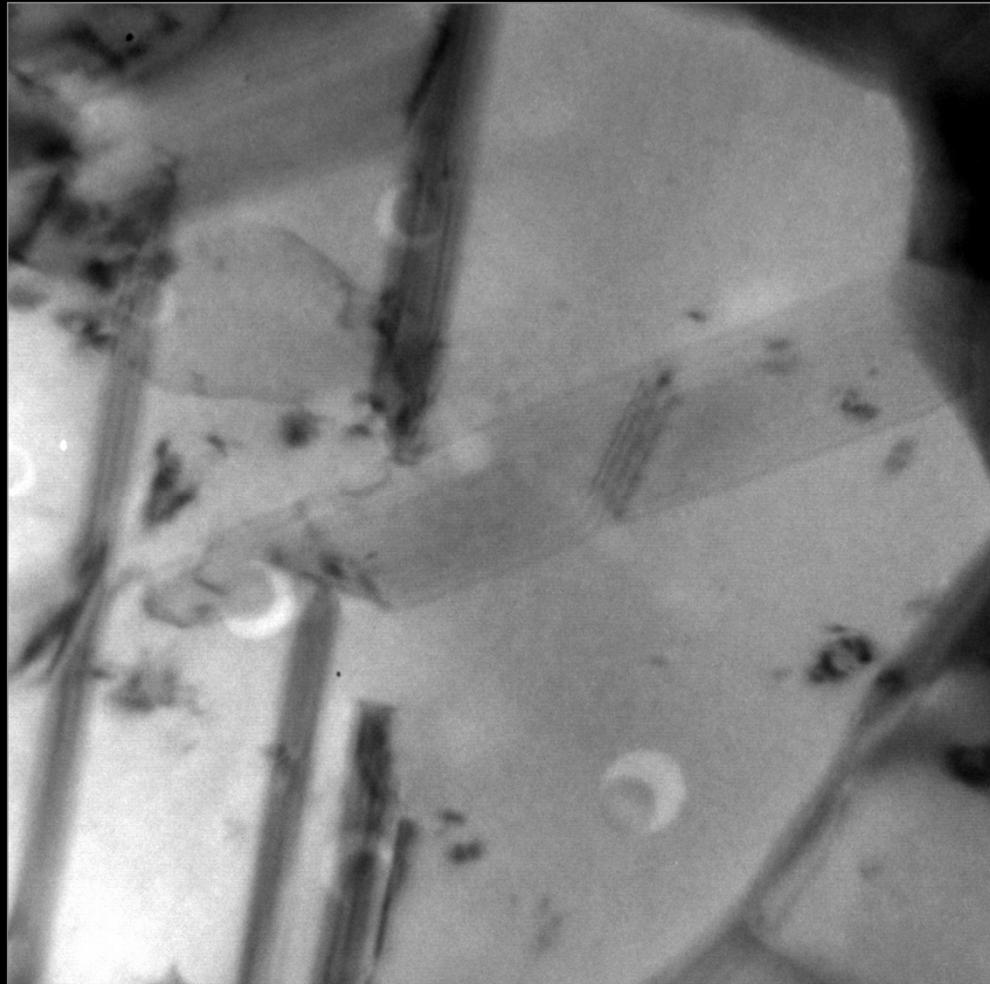
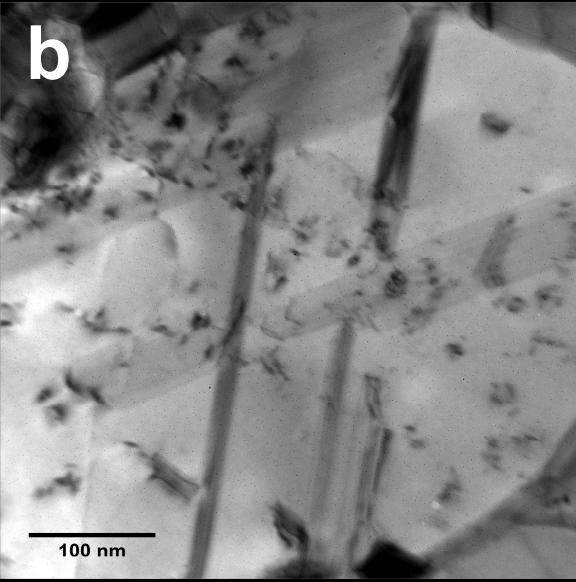
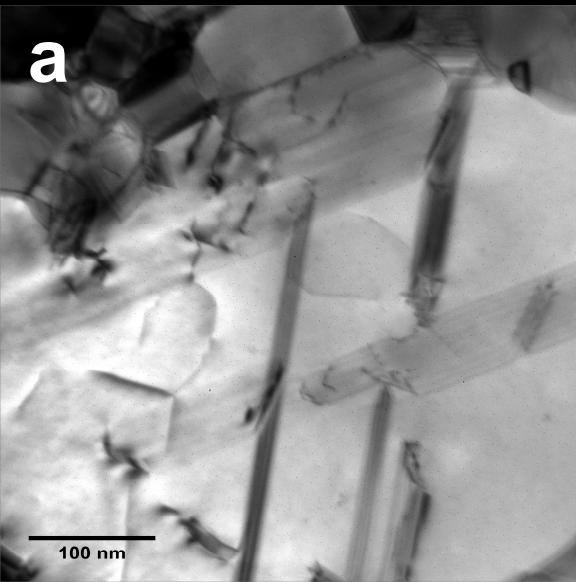
Successive He<sup>1+</sup> then Au<sup>4+</sup>



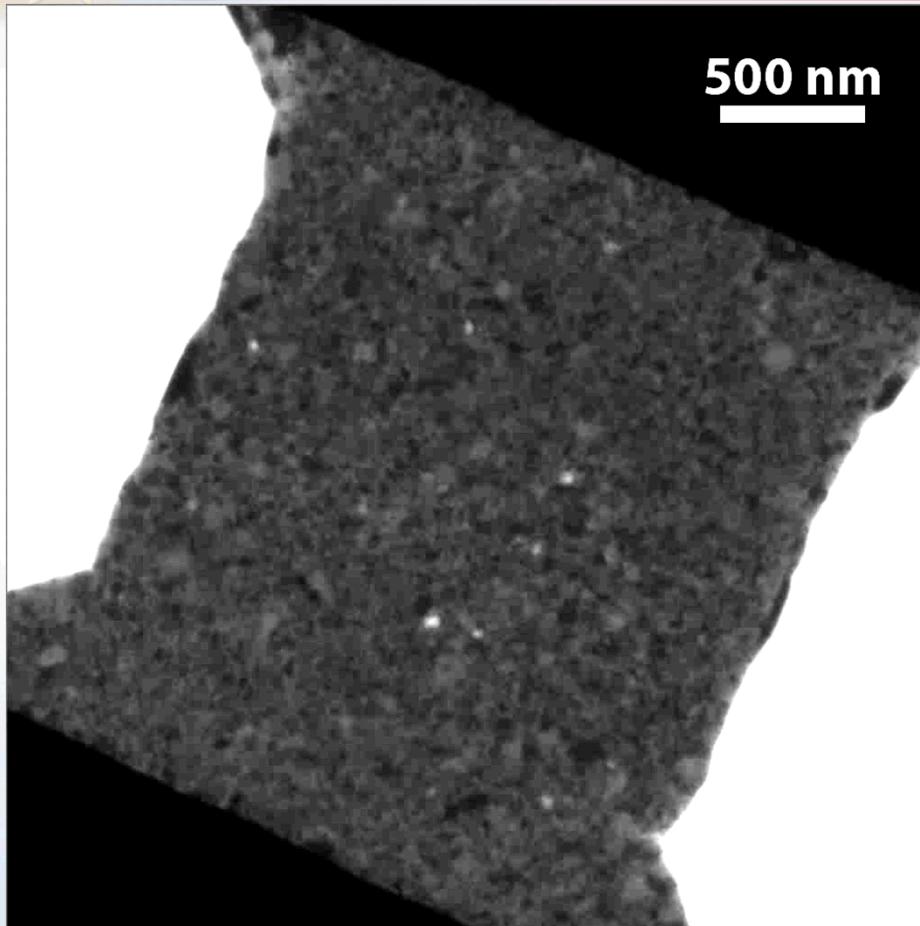
# *In situ* Concurrent Implantation & Irradiation

Collaborators: C. Chisholm & A. Minor

**He<sup>+</sup> implantation and concurrent Au<sup>4+</sup> irradiation:  
Transient bubble formation and dissolution**



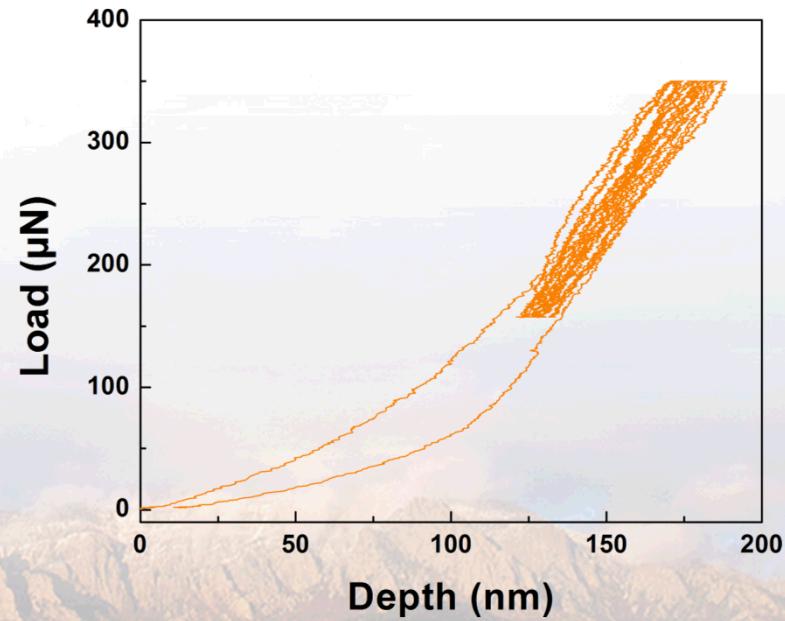
# In Situ Tensile Testing



- Slow crack propagation
- Evidence of grain growth

## ■ Cyclic loading:

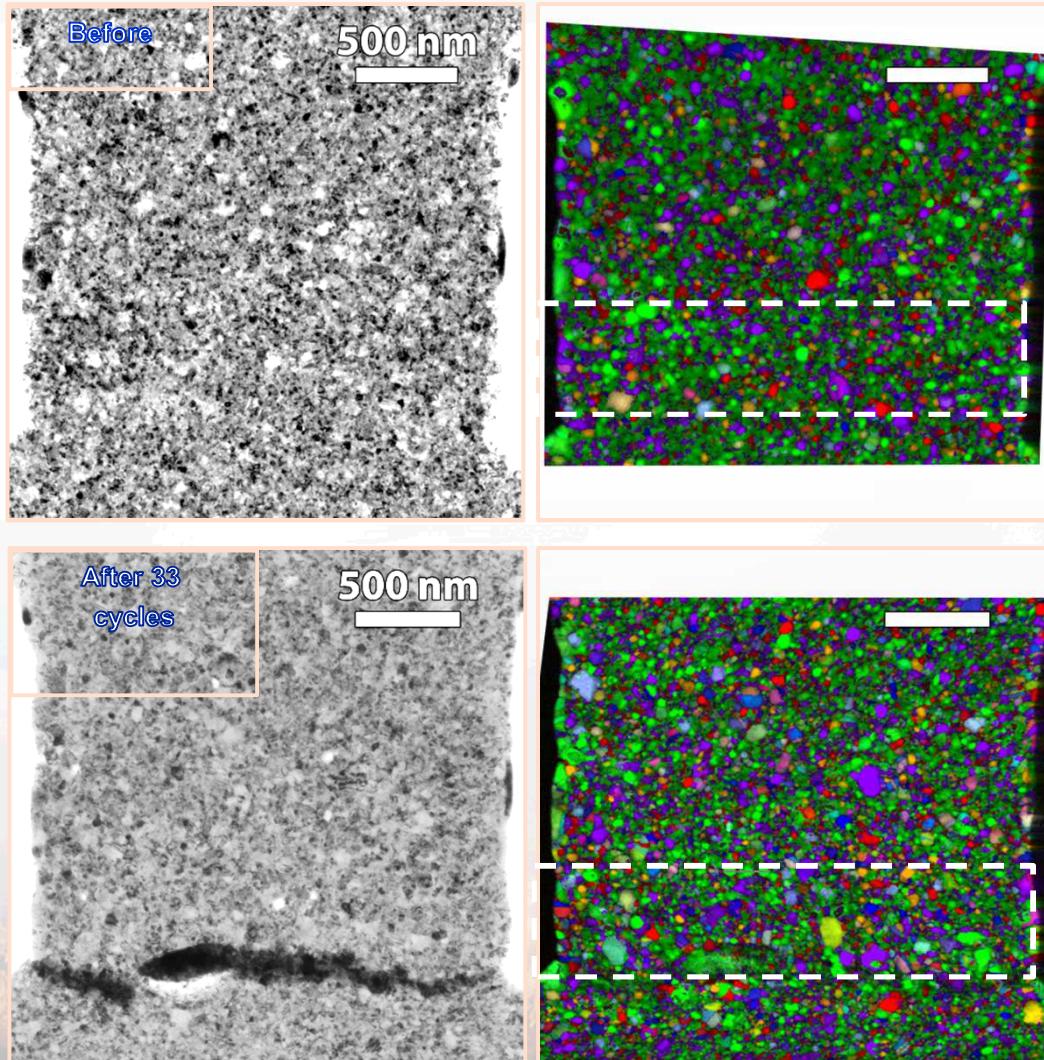
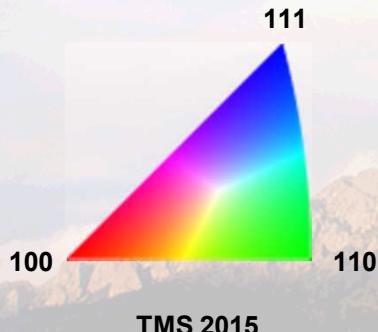
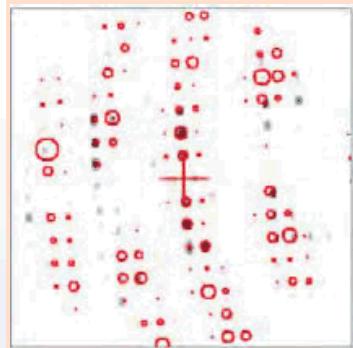
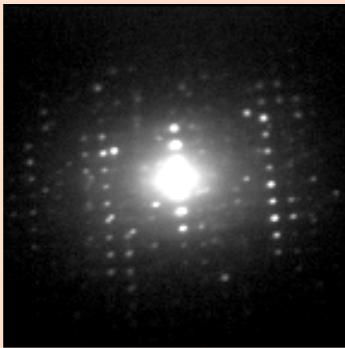
- Crack initiated in previous monotonic test
- 9 cycles to  $\sim 87.5\%$  of that load
- 50 % unloading
- Slow crack propagation



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# Precession Diffraction: Quantifying Microstructural Change

- Combining orientation mapping with deformation
- EBSD-like capability in the TEM
  - Powerful analytical tools available



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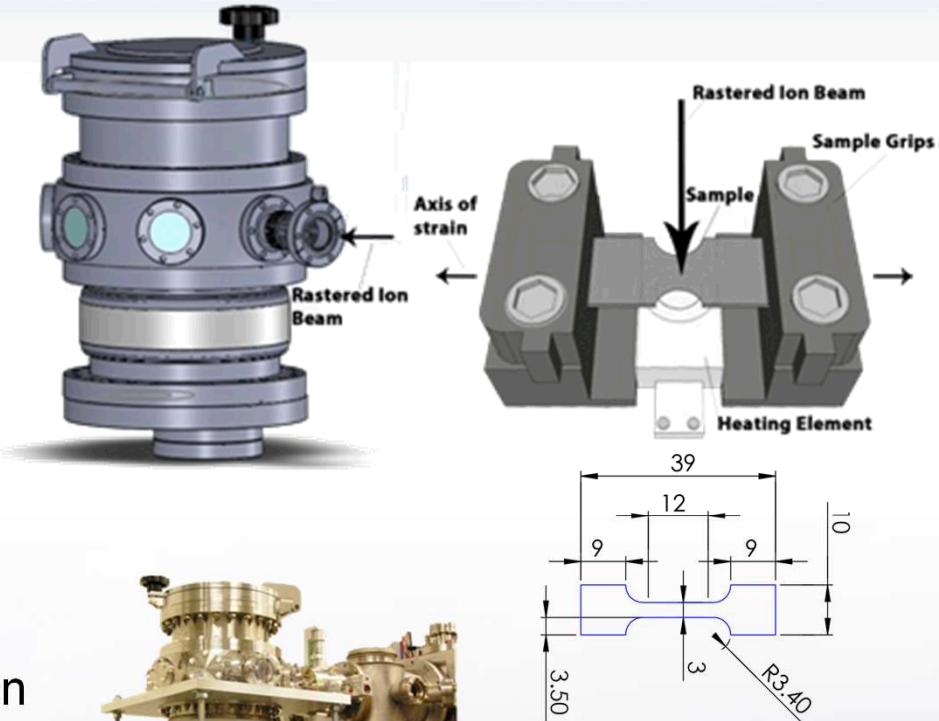
# Extreme Environments at the Meso Scale

## ■ Meso-scale mechanical test

- Straining + Heating stage
- Ions from the 6MV Tandem
- Heating to 800C

## ■ 30 GPa stress, 58% strain

- Geometry based on ASTM-E8
- 50 – 100  $\mu\text{m}$  sample thickness
- Limited to 4.5MeV protons by radiation levels (neutron production by SS)

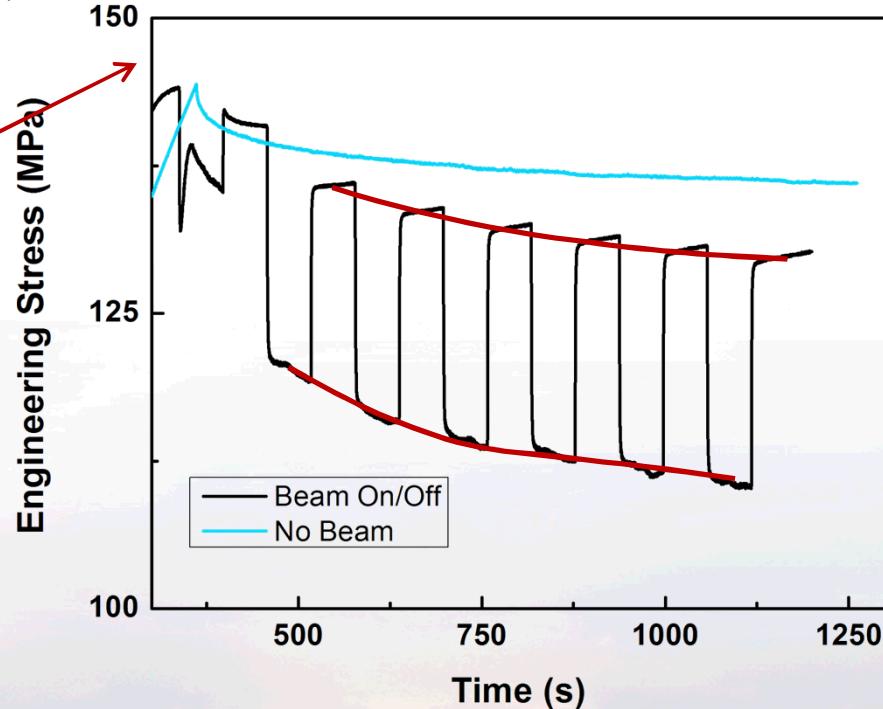
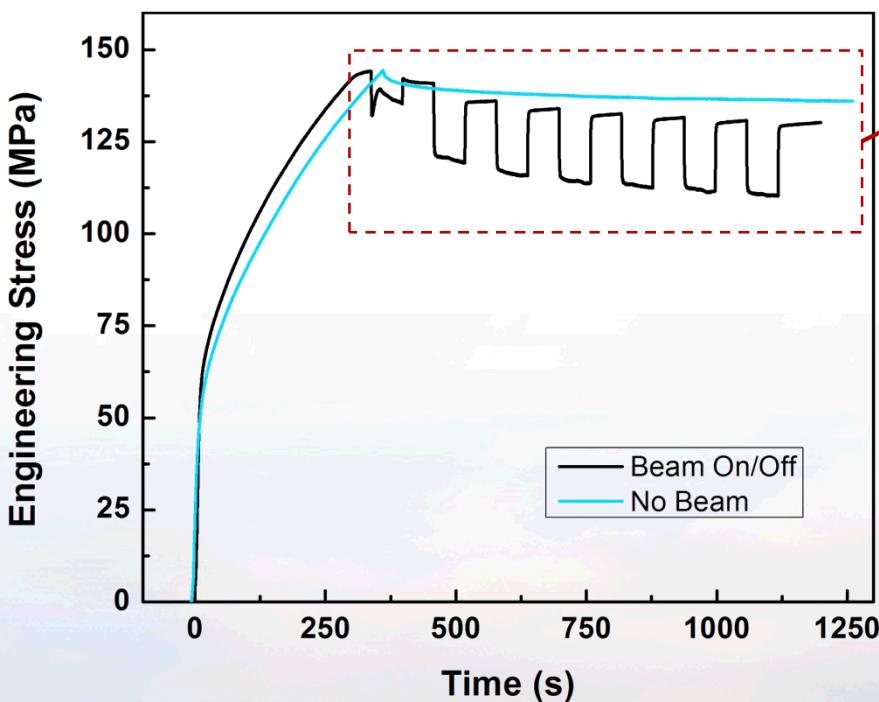


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# Copper Stress Relaxation with/without Irradiation

## ■ Commercial OHFC Copper, 50 $\mu$ m thick

- Similar 0.25mm/min elongation rate to 22.5 N load
- Approximately 75% of typical ultimate tensile load
- 4.5 MeV protons have projected range of 65 $\mu$ m



- Preliminary data – still optimizing configuration
- Different relaxation rates with beam on and off



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# Summary

- **Sandia has developed unique in-situ experimental capability**
- **I3TEM – *In situ* experimental workhorse**
  - Dual, colinear ion beams (keV to MeV)
  - Broad array of stages to tailor environment
  - Detailed microstructure characterization
  - Mechanical characterization
- **Meso-scale mechanical properties**
  - Straining + heating stage
  - MeV ion beam for defect generation or implantation



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